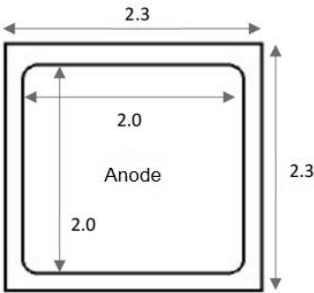


Physical Characteristics

	Die size: 2.3 mm x 2.3 mm (without scribe line) Anode pad open size: 2.0 mm x 2.0 mm Gross die / per 6" wafer =2627pcs
	Main characteristics: $V_{RRM} = 1200V$ $I_F(T_C=140^{\circ}C) = 10A$ $Q_C = 55nC$

Mechanical Data

Parameter	Parameter
Nominal Back Metal Composition, Thickness	Ti- Ni - Ag(1.4 μ m)
Nominal Front Metal Composition, Thickness	Al(4.2 μ m)
Wafer Diameter	150mm
Wafer Thickness	175 μ m
Scribe line width	100 μ m
Passivation	Polyimide

Absolute Maximum Ratings($T_C=25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Test Condition	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		1200	V
Continuous Forward Current	I_F	$T_C= 25^{\circ}C, D=1$	32	A
		$T_C= 100^{\circ}C, D=1$	18	
		$T_C= 140^{\circ}C, D=1$	10	
Non-Repetitive Forward Surge Current	I_{FSM}	$T_C= 25^{\circ}C, t_p =10ms$	70	A
		$T_C= 125^{\circ}C, t_p =10ms$	58	
Repetitive Forward Surge Current	I_{FRM}	$T_C= 25^{\circ}C, t_p =10ms$	45	A
		$T_C= 125^{\circ}C, t_p =10ms$	33	
Power Dissipation	P_{tot}	$T_C= 25^{\circ}C$	160	W
Operating and Storage Temperature	T_J, T_{STG}		-55 to 175	$^{\circ}C$

Note: All characteristics are tested with the parts assembled in TO-247-2 package, and exposure to absolute maximum ratings for prolonged time periods may affect device reliability.

Electrical Specifications($T_C=25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse Blocking Voltage	V_R	$I_R =250\mu A$	1200			V
Reverse Current	I_R	$V_R =1200V, T_J = 25^{\circ}C$		5	50	μA
		$V_R =1200V, T_J = 150^{\circ}C$		25	100	
Forward Voltage	V_F	$I_F =10A, T_J = 25^{\circ}C$		1.45	1.7	V
		$I_F =10A, T_J = 150^{\circ}C$		1.9	2.5	